

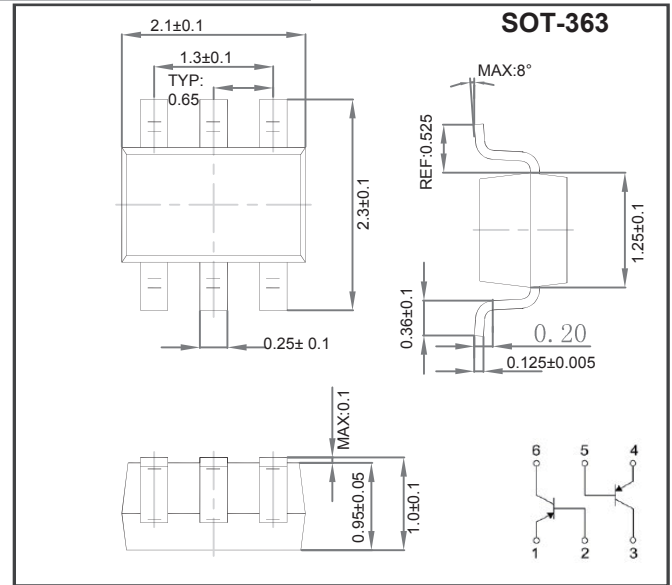
SOT-363 Plastic-Encapsulate Transistors

Features

- Two transistors in one package
- Reduces number of components and board space
- No mutual interference between the transistors

MECHANICAL DATA

- Case style: SOT-363 molded plastic
- Mounting position: any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameters	Symbol	Value	Unit
Collector-Base Voltage	V_{CB0}	-80	V
Collector-Emitter Voltage	V_{CEO}	-65	V
Emitter -Base Voltage	V_{EBO}	-5	V
Collector Current-Continuous	I_C	-100	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55-+150	°C
Thermal resistance From junction to ambient	$R_{\theta JA}$	625	°C/W

Electrical Characteristics (Ratings at 25°C ambient temperature unless otherwise specified).

Parameter	Symbols	Test Condition	Limits			Unit
			Min		Max	
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu A, I_E = 0$	-80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-65			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -30V, I_E = 0$			-15	nA
Base cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-100	nA
DC current gain	h_{FE}	$V_{CE} = -5V, I_C = -2mA$	110			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10mA, I_B = -0.5mA$			-0.1	V
		$I_C = -100mA, I_B = -5mA$			-0.3	V
Base -emitter saturation voltage	$V_{BE(sat)}$	$I_C = -10mA, I_B = -0.5mA$		0.7		V
Transition frequency	f_T	$V_{CE} = -5V, I_C = -10mA, f = 100MHz$	100			MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$			2.5	pF

*Pulse test: pulse width $\leq 350\mu s$, duty cycle $\leq 2.0\%$



RATINGS AND CHARACTERISTIC CURVES

■ Typical Characteristics

